

Status and plan of Si pixel detector

*New funding from MOST (2016-2021)

- R&D targeting on
 - σ_{sp} 3-5 μm
 - *Power consumption < 100mW/cm²*
 - *Integration time 10-100 μs*

- CMOS pixel sensor (CPS)
 - *Small pixel size*
 - *In-pixel functional circuitry*
 - *Novel readout scheme → faster & less power*
 - *Full functional chip*
 - *~2 MPW and 1 engineering run*
 - *TowerJazz CiS 0.18 μm process*

Charge collection simulation

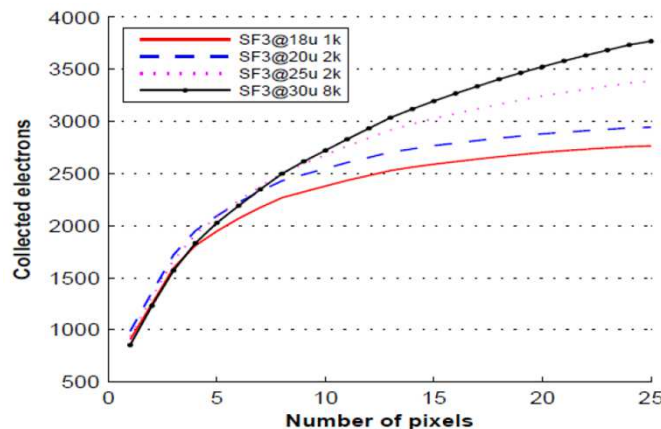
Y.Zhang, et al, NIMA 831(2016)99-104

Motivation:

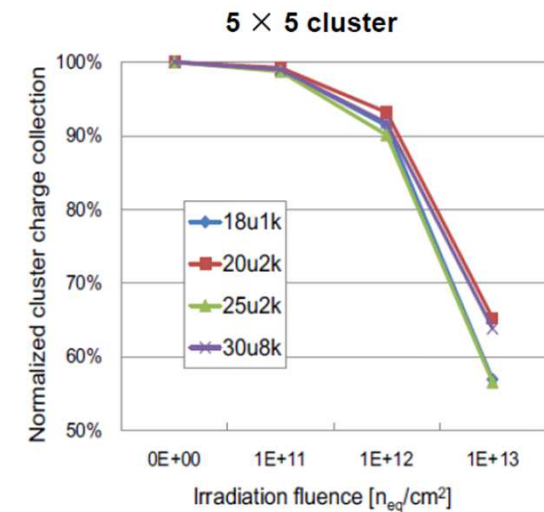
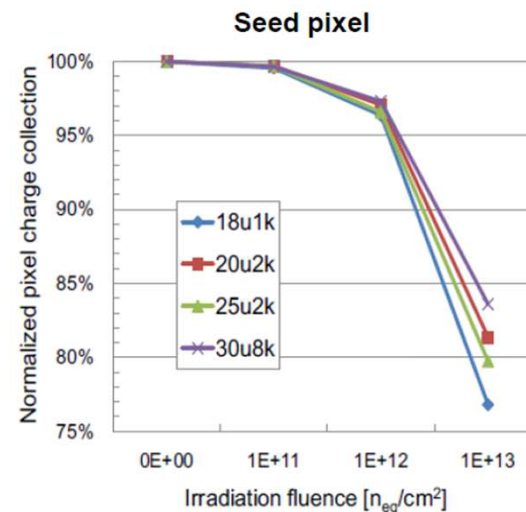
- Guide the diode geometry optimization and study radiation damage with different types of epitaxial layer

Simulation with different parameters

- Hit position
- Diode geometry
- Thickness and resistivity of the epitaxial layer
- Radiation damage



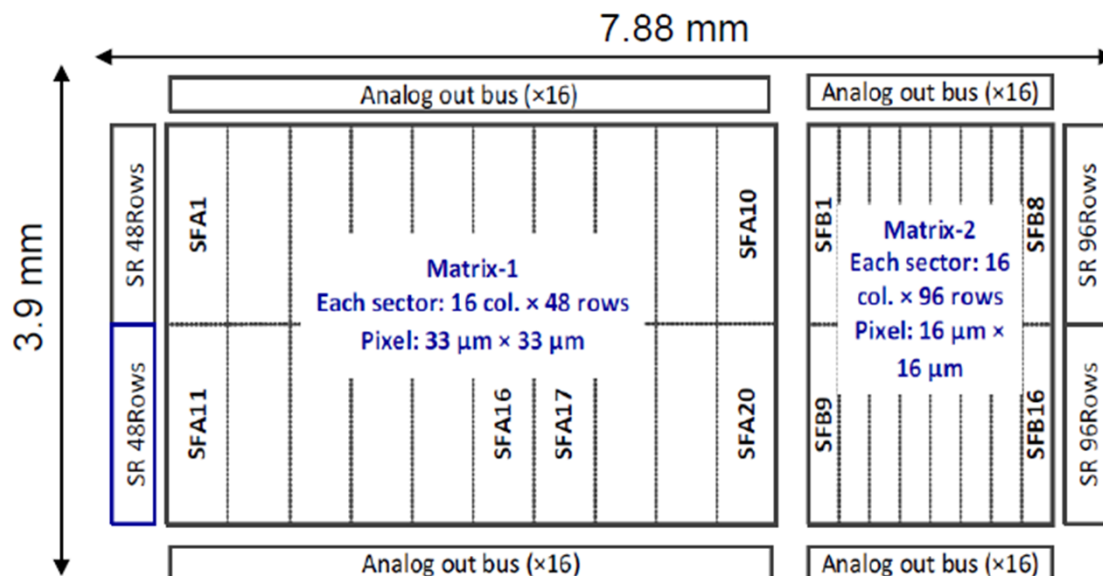
Pixel cluster with four different epitaxial layers



Charge collection with non-ionizing damage

1st CPS prototype design

- Goals: sensor optimization and in-pixel pre-amplifier study
- Floorplan overview:
 - Two independent matrices: Matrix-1 with $33 \times 33 \mu\text{m}^2$ pixels (except one sector SFA20 with $16 \times 16 \mu\text{m}^2$ pixels), Matrix-2 with $16 \times 16 \mu\text{m}^2$ pixels.
 - Matrix-1 includes 3 blocks with in-pixel pre-amplifier
 - SFA20 in Matrix-1 contains pixel with AC-coupled pixels



- Tower Jazz CIS $0.18 \mu\text{m}$, November 2015 submission
- Two types of wafer:
 - $18 \mu\text{m}$ HRES epi-layer wafer
 - 700Ω Czochralski wafer
- Sensor arrival at IHEP
- Test board and system in preparation, including the NIEL measurement.

2nd CPS prototype design

IHEP: Y. Zhang, Y. Zhou
CCNU: P. Yang

- Purpose: small-size digital pixel design verification, fast readout
- Pixel design:
 - Pixel size: smaller than $22 \times 22 \mu\text{m}^2$
 - Each pixel contains a sensing diode, a pre-amplifier and a discriminator
 - AC coupling: rolling-shutter readout with higher biased voltage
 - DC coupling: asynchronous readout with high gain and low noise
- Readout design:
 - Matrix readout using XYZ solution
 - Pixel size: $26 \times 26 \mu\text{m}^2$
 - Signal duration time: $< 3 \mu\text{s}$
 - Readout speed: 25 ns/hit
 - Power consumption: $< 80 \text{ mW/cm}^2$

Proposed area

DC coupling pixel design +
XYZ readout scheme

4.6 mm

AC coupling pixel
design

3.6 mm

3.2 mm

CCNU

IHEP

$\sim 26.3 \text{ mm}^2$

MPW submission: Feb., 2017

Items to be addressed in the future

- Sensor characterization needs more time.
- Overall sensor architecture should be considered now.
- Optimization study of vertex system will be critical.
- CDR requirements needs to be raised.
- Possible changes of sensor design
 - *Beam related background level*
 - *Impact of partial-double ring scheme, with time-stamp of microsecond*
 - *Impact of Z-pole running*